

RB721Q-40

PRV : 40 Volts

I_o : 30 mA

FEATURES :

- * Silicon epitaxial planar
- * Low forward voltage
- * Small pitch enables insertion on PCBs.
- * Glass sealed envelop for high reliability
- * Pb / RoHS Free

APPLICATIONS :

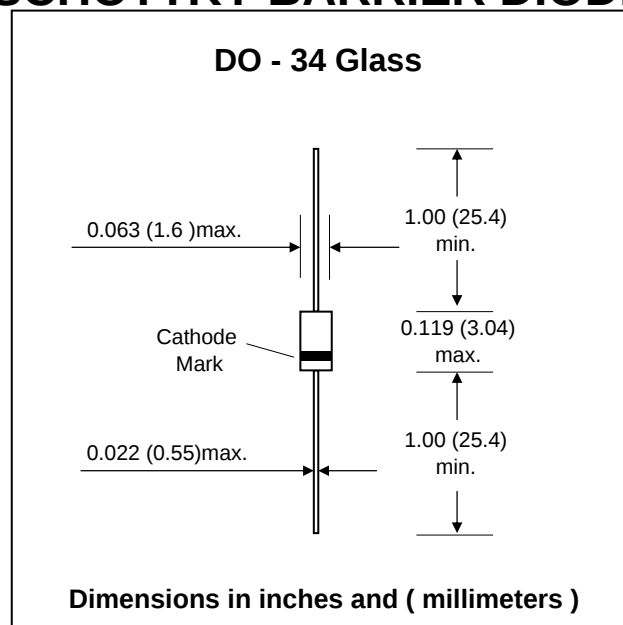
- * High speed switching

MECHANICAL DATA :

* Case: DO-34 Glass Case

* Weight: approx. 0.11g

SCHOTTKY BARRIER DIODE



Maximum Ratings and Thermal Characteristics (Ta = 25 °C)

Parameter	Symbol	VALUE	Unit
Maximum DC Reverse Voltage	V_R	40	V
Maximum Peak Reverse Voltage	V_{RM}	40	V
Maximum Forward Current	I_F	30	mA
Maximum Peak Forward Surge Current (60 Hz for sine wave)	I_{FSM}	200	mA
Junction Temperature	T_J	125	°C
Storage temperature range	T_{STG}	-40 to + 125	°C

Electrical Characteristics (Ta = 25 °C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Current	I_R	$V_R = 25$ V	-	-	0.5	μ A
Forward Voltage	V_F	$I_F = 1$ mA	-	-	0.37	V
Capacitance between terminals	C_T	$V_R = 1$ V, $f = 1$ MHz	-	2.0	-	pF

RATING AND CHARACTERISTIC CURVES (RB721Q-40)

FIG.1 - DERATING CURVE

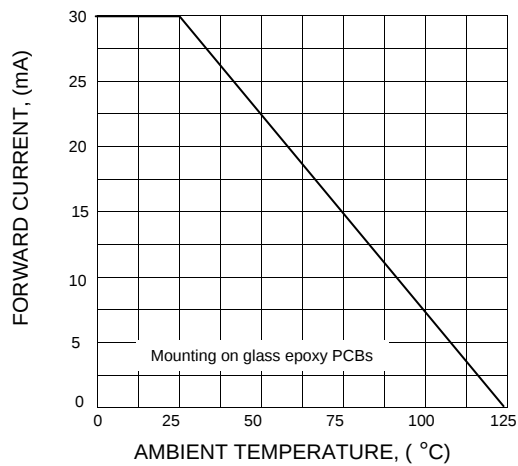


FIG.2 - CAPACITANCE BETWEEN TERMINALS CHARACTERISTICS

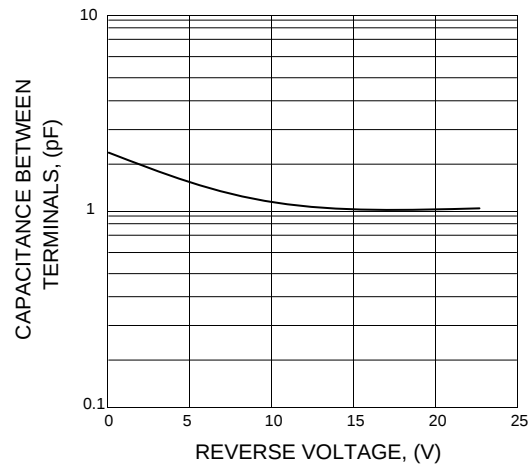


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

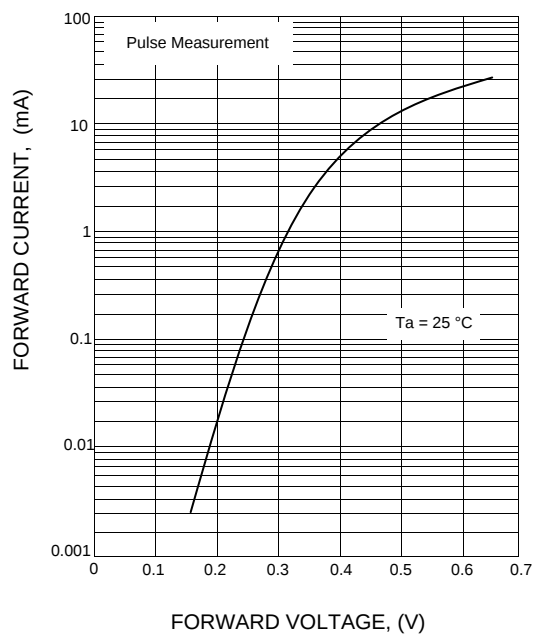


FIG. 4 - TYPICAL REVERSE CHARACTERISTICS

